L Number	Hits	Search Text	DB	Time stamp
1	44	5676587.pn. 5853604.uref. 5827781.uref.	USPAT;	2004/04/27 17:04
		,	US-PGPUB	
2	10	5733177.uref.	USPAT;	2004/04/27 17:07
_			US-PGPUB	
3	21	(((cmp (chemical near mechanical)) with (copper cu	USPAT;	2004/04/27 17:08
		conduct\$4 metal))) same (relative near2 (speed velocity))	US-PGPUB	
4	144	((438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls.	USPAT;	2004/04/27 17:10
	-	438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative	US-PGPUB	
		near2 (speed velocity))) and ((cmp (chemical near		
		mechanical)) with (copper cu conduct\$4 metal))		
5	9	((438/626.ccls. 438/633.ccls. 438/687.ccls.) and	USPAT;	2004/04/27 17:16
	·	(438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.))	US-PGPUB	
		and (relative near2 (speed velocity))		
6	34	(((cmp (chemical near mechanical)) with (copper cu	USPAT;	2004/04/27 17:17
		conduct\$4 metal))) same ((relative linear) near2 (speed	US-PGPUB	
		velocity))		0004/04/07 := 0:
7	29	(((cmp (chemical near mechanical)) with (copper cu	USPAT;	2004/04/27 17:21
		conduct\$4 metal))) same ((rotat\$6 near2 (speed velocity))	US-PGPUB	
		rpm rpms) same (change decreas\$4 reduc\$5)		2004/04/27 47:22
8	4	(((cmp (chemical near mechanical)) with (copper cu	EPO; JPO;	2004/04/27 17:22
		conduct\$4 metal))) and (relative near2 (speed velocity))	DERWENT;	
		/ / / to to to a second section in the back (Approximate	IBM_TDB	2004/04/27 17:22
9	127	(cmp (chemical near mechanical) polish\$4) and ((carrier	USPAT;	2004/04/27 17:22
		head) same (retain\$4 ring) same membrane same (platen	US-PGPUB	
	161	pad) same (pressure psi pa)) and (wafer substrate)	LICDAT.	2004/04/27 17:31
10	161	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls.	USPAT; US-PGPUB	2004/04/2/ 17.31
		438/691.ccls. 438/692.ccls. 451/41.ccls.) and (((cmp (chemical near mechanical) polish\$4) with (copper cu	03-PGP06	
		(chemical hear mechanical) polish \$4) with (copper cu conduct\$4 metal)) and ((carrier head) same (retain\$4 ring		,
		membrane) same (platen pad) same (pressure psi pa)) and		
		(wafer substrate))		
11	141	((cmp (chemical near mechanical) polish\$4) and ((carrier	EPO; JPO;	2004/04/27 17:37
11	141	head) same (retain\$4 ring membrane)) and (platen pad))	DERWENT;	
		and (pressure psi pa copper cu metal conduct\$4)	IBM_TDB	
12	6	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2004/04/27 17:40
		substrate) and ((carrier head) same (platen pad) same (rpm	US-PGPUB	
		adj second))		
13	0	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2004/04/27 17:41
		substrate) and ((carrier head) same (platen pad) same	US-PGPUB	
:		((rpm rotat\$6) near accelerat\$5))		
14	2	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2004/04/27 17:41
		substrate) and ((carrier head) same (platen pad) same	US-PGPUB	
		((rpm rotat\$6) with accelerat\$5))		2004/04/25
15	30	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2004/04/27 17:41
		substrate) and ((carrier head) same (platen pad) same	US-PGPUB	
. .		accelerat\$5)	LICDAT	2004/04/27 47:42
16	519	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls.	USPAT;	2004/04/27 17:42
		438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative	US-PGPUB	
		near2 (speed velocity))	LICDAT	2004/04/27 17:53
17	683	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls.	USPAT; US-PGPUB	2007/09/2/ 17:53
		438/691.ccls. 438/692.ccls. 451/41.ccls.) and ((cmp (chemical near mechanical) polish\$4) and ((carrier head)	USTRUPUB	
		(chemical hear mechanical) polish(\$4) and ((carrier head) same (retain(\$4 ring membrane)) and (wafer substrate) and		
		(platen pad))		
	1	(Plateir Pau))	<u></u>	I